

Form 1449*	Atty. Docket No.: 303.684US2	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes	10/04/2924
	Filing Date: Herewith 01/09/02	Group: Unknown
		2813
		11002/42924
		01/09/02

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Examiner

*Walter Allegre*

Date Considered

7-11-2003

\*Substitute Disclosure Statement Form (PTO-1449)

\*\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Examiner

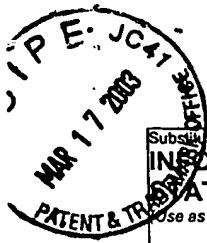
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Substitute for form 1449A/PTO  
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 STATEMENT BY APPLICANT**  
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Complete if Known

Application Number	10/042924
Filing Date	January 9, 2002
First Named Inventor	Forbes, Leonard
Group Art Unit	2822 2813
Examiner Name	Unknown VESPERMAN

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Attorney Docket No: 303.684US2

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